

isc Silicon PNP Darlington Power Transistor

2SB1286

DESCRIPTION

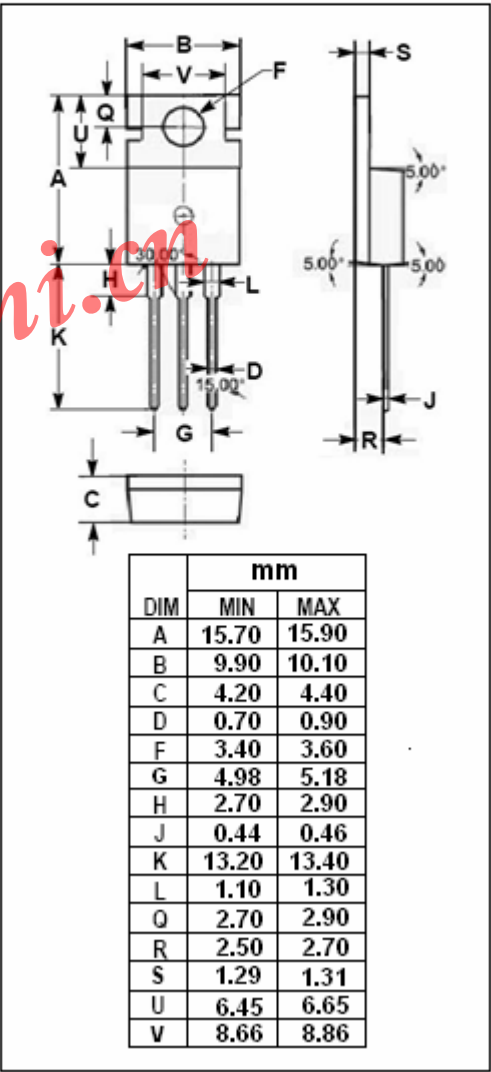
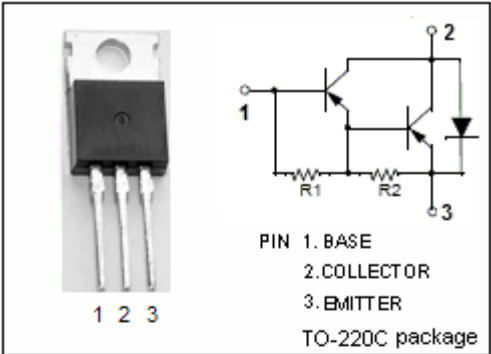
- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ I_C = -1A$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- Low Collector-Emitter Saturation Voltage
: $V_{CE(sat)} = -1.5V(\text{Max}) @ I_C = -1A$
- Complement to Type 2SD1646

APPLICATIONS

- Designed for general purpose amplifier and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Collector Power Dissipation $T_C = 25^\circ C$	25	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -5\text{mA}$, $I_B = 0$	-100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -50\text{ }\mu\text{A}$, $I_E = 0$	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}$; $I_B = -1\text{mA}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -100\text{V}$; $I_E = 0$			-10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -7\text{V}$; $I_C = 0$			-3	mA
h_{FE}	DC Current Gain	$I_C = -1\text{A}$; $V_{CE} = -2\text{V}$	1000		10000	
C_{OB}	Output Capacitance	$I_E = 0$; $V_{CB} = -10\text{V}$; $f = 1\text{MHz}$		35		pF